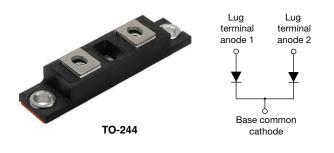
**Vishay Semiconductors** 

## HEXFRED<sup>®</sup> Ultra Fast Soft Recovery Diode, 320 A



www.vishay.com

#### FEATURES

- Very low Q<sub>rr</sub> and t<sub>rr</sub>
- UL approved file E222165



Designed and qualified for industrial level
Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

#### **DESCRIPTION / APPLICATIONS**

HEXFRED<sup>®</sup> diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl<sub>F</sub>/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

PRIMARY CHARACTERISTICS				
320 A				
400 V				
255 A at 85 °C				
TO-244				
Two diodes common cathode				

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS		MAX.	UNITS	
Cathode to anode voltage	VR		400	V	
		T <sub>C</sub> = 25 °C	420		
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 85 °C	255	^	
		T <sub>C</sub> = 115 °C	160	A	
Single pulse forward current	I <sub>FSM</sub>	Limited by junction temperature	1200		
Non-repetitive avalanche energy	E <sub>AS</sub>	L = 100 $\mu$ H, duty cycle limited by maximum T <sub>J</sub>	1.4	mJ	
		T <sub>C</sub> = 25 °C	625		
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	250	W	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		400	-	-	
		I <sub>F</sub> = 160 A		-	1.10	1.35	V
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 320 A	See fig. 1	-	1.30	1.54	
		I <sub>F</sub> = 160 A, T <sub>J</sub> = 125 °C		-	1.00	1.20	
Maximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 400 V	See fig. 2	-	0.9	3	mA
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	370	500	pF
Series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane		-	5.0	-	nH

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 Document Number: 94072

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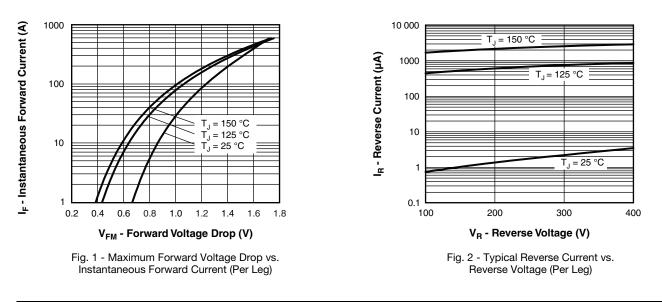
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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	45	-	
Reverse recovery time See fig. 5		7 T T T T T T T T T T T T T T T T T T T	-	90	140	ns	
eee ligi e		T <sub>J</sub> = 125 °C		-	290	440	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	8.7	20	А
See fig. 6		IRRM	T <sub>J</sub> = 125 °C	$I_{\rm F} = 160  {\rm A}$	-	18	30
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 200 V	-	420	1100	nC
See fig. 7		Qrr	T <sub>J</sub> = 125 °C		-	2600	7000
Peak rate of recovery current See fig. 8	dl <sub>(rec)M</sub> /dt	الم الم	T <sub>J</sub> = 25 °C		-	300	-
		T <sub>J</sub> = 125 °C		-	280	-	A/µs

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>	- 55	-	150	°C	
Thermal resistance, junction to case	per leg	P	-	-	0.19	°C/W K/W	
	per module	– R <sub>thJC</sub>	-	-	0.095		
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	-	0.10	-		
\//-:			-	68	-	g	
Weight			-	2.4	-	oz.	
Mounting torgue <sup>(1)</sup>			30 (3.4)	-	40 (4.6)		
Mounting torque (*)	center hole		12 (1.4)	-	18 (2.1)	lbf · in (N · m)	
Terminal torque			30 (3.4)	-	40 (4.6)	()	
Vertical pull			-	-	80	llef in	
2" lever pull			-	-	35	lbf · in	

#### Note

(1) Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film or thermal grease to mounting surface. Gradually tighten each mounting bolt in 5 to 10 lbf · in steps until desired or maximum torque limits are reached.



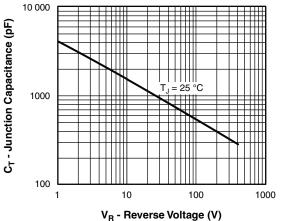
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V<sub>R</sub> - neverse voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

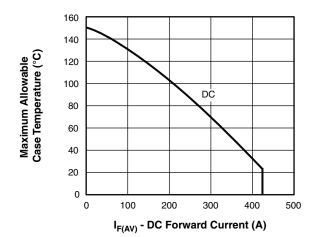


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current (Per Leg)

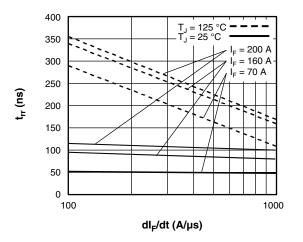


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

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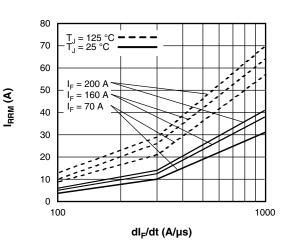
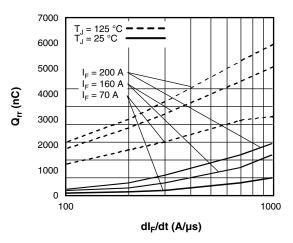
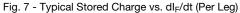


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt (Per Leg)





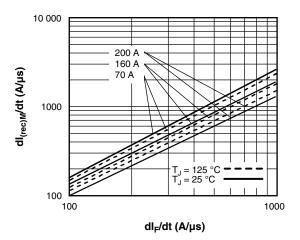


Fig. 8 - Typical dI(rec)M/dt vs. dIF/dt (Per Leg)

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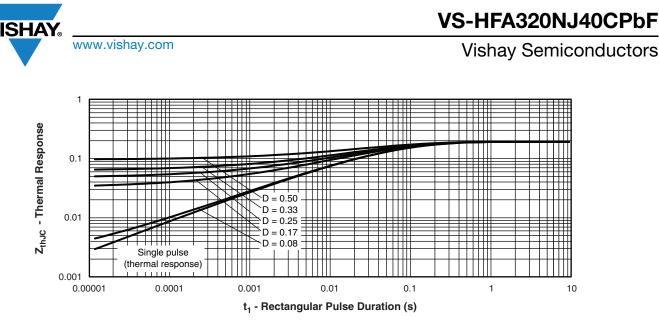


Fig. 9 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

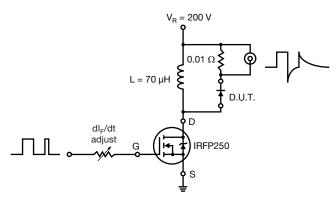
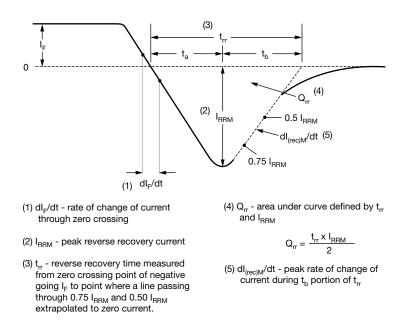


Fig. 10 - Reverse Recovery Parameter Test Circuit







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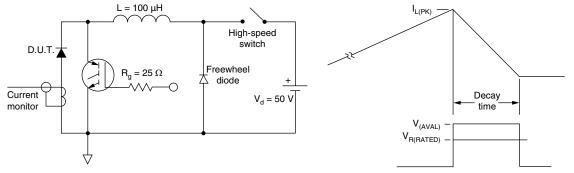
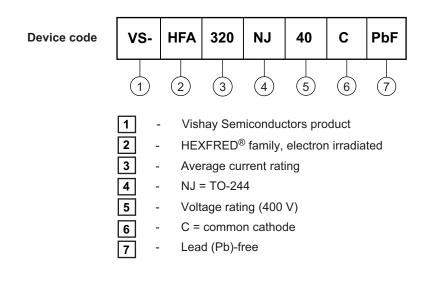


Fig. 12 - Avalanche Test Circuit and Waveforms

#### **ORDERING INFORMATION TABLE**



LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95021			

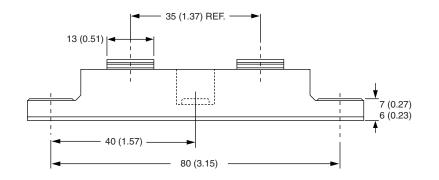


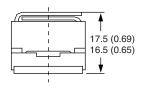


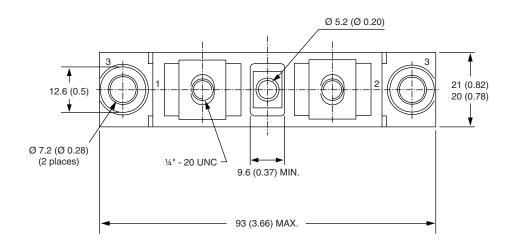
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**TO-244** 

#### **DIMENSIONS** in millimeters (inches)









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